## B.TECH/CSE/8<sup>TH</sup> SEM/ECEN 4283/2019 VLSI TESTING AND VERIFICATION (ECEN 4283)

Tiı	ne Allo	tted : 3 hrs Full Marks : 70			
Figures out of the right margin indicate full marks.					
	Candidates are required to answer Group A and <u>any 5 (five)</u> from Group B to E, taking <u>at least one</u> from each group.				
Candidates are required to give answer in their own words as far as practicable.					
Group – A (Multiple Choice Type Questions)					
1.	Choose	the correct alternative for the following: <b>10 × 1 = 10</b>			
	(i)	$ \begin{array}{lll} \mbox{For Sub Micron Technology } L_{gate} & (Channel Length) \mbox{ is} \\ (a) > 100 \mbox{ nm} & (b) < 100 \mbox{ nm} & (c) > 1 \mbox{ \mu m} & (d) \mbox{ None of these.} \end{array} $			
	(ii)	Output of physical design is(a) circuit(b) layout(c) logical model(d) RTL schematic.			
	(iii)	In PVT analysis the variational sources considered are,, andtemperature.(a) pressure, volume(b) progress, value(c) process, voltage(d) performance, volume.			
	(iv)	A MOS device can be used as a resistor in(a) linear Region(b) saturation region(c) sub-threshold condition(d) mask region.			
	(v)	ATPG is based on (a) stuck at fault (b) BIST (c) bridging fault (d) DFT.			
	(vi)	As per Moore's Law, area of transistor is scaled by (a) 0.5 (b) 0.6 (c) 0.9 (d) 0.7.			
	(vii)	A short between two elements is referred to as (a) timing fault (b) bridging fault (c) series fault (d) decision fault.			
	(viii)	The noise immunity of the circuit with noise margin. (a) increases (b) decreases (c) is constant (d) zeros.			
	(ix)	CMOS stands for Metal Oxide Semiconductor (a) Complementory (b) Common (c) Curious (d)Controlled.			

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(x)	(a) logic design (c) layout design	(b) circuit design (d) architecture design.
	Gi	coup – B
2. (a)	Explain with schematic the operation of a CMOS inverter. Describe its VTC characteristics. What are its advantages over other MOS inverters?	
(b)	Design a CMOS based 2 inp and nMOS network.	ut NOR gate, explaining operation of the pMOS
		7 + 5 = 12
3. (a)	Implement 2 input AND gate	e using Pass Transistor Logic.
(b)	Implement 2 input XOR gate	using Transmission Gate (TG) Logic. 6 + 6 = 12
	G	roup – C
4. (a)	Sketch the Y chart for simpli	fied VLSI design flow in three domains.
(b)	In VLSI, what are full-custom and semi-custom designs and design with FPGA?	
(c)	In VLSI design, explain the c	oncepts of regularity, modularity, and locality.
		4+4+4=12
5. (a)	What is Moore's law?	
(b)	Draw cross sectional diagra	m of a CMOS Inverter.
(c)	Draw schematic diagram of	a 3-input NAND Gate.
(d)	Draw stick diagram of same	e 3-input NAND gate.
		2+3+2+5=12
	Gr	oup – D
6. (a)	What are DRC and LVS?	
(b)	Why do we need post layout	timing verification?
(c)	Define setup time and hold t	ime of a D-Latch.
(d)	What is process variation?	
		3+3+3+3=12
7 (a)	Explain the effects of gate d	elay fault? What is the critical path in a circuit?

(a) Explain the effects of gate delay fault? What is the critical path in a circuit?What is meant by the capture path?

(b) What is clock skew and what are the sources of clock skew?

8 + 4 = 12

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## Group – E

- 8. (a) Why is post Si debugging needed ?
- (b) Explain D-Algorithm with an example circuit.

6 + 6 = 12

9. (a) Using ATPG time frame expansion method, generate primary input test patterns for the S-a-0 fault, at the line j in the sequential circuit given below.



(b) Using ATPG path sensitization, generate primary input test patterns for the S-a-0 fault, at line d in the combinational circuit given below.



8+4 = 12